

# MOSFET – N-Channel, Shielded Gate, POWER trench® 150 V, 62 A, 12.4 mΩ

## FDMS86255

### Description

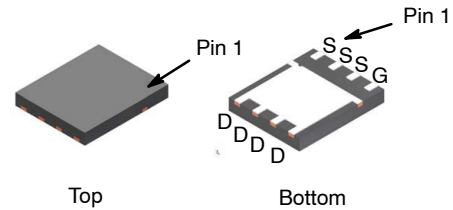
This N-Channel MOSFET is produced using **onsemi** advanced POWER trench process that incorporates Shielded Gate technology. This process has been optimized for the on-state resistance and yet maintain superior switching performance.

### Features

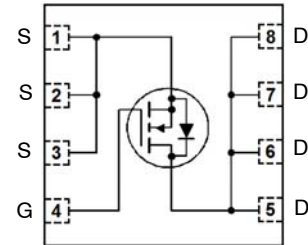
- Shielded Gate MOSFET Technology
- Max  $R_{DS(on)}$  = 12.4 mΩ at  $V_{GS}$  = 10 V,  $I_D$  = 10 A
- Max  $R_{DS(on)}$  = 15.5 mΩ at  $V_{GS}$  = 6 V,  $I_D$  = 8 A
- Advanced Package and Silicon Combination for Low  $R_{DS(on)}$  and High Efficiency
- Next Generation Enhanced Body Diode Technology, Engineered for Soft Recovery
- MSL1 Robust Package Design
- 100% UIL Tested
- RoHS Compliant
- These Device is Halogen Free

### Applications

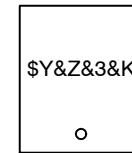
- OringFET / Load Switching
- Synchronous Rectification
- DC–DC Conversion



PQFN8 5X6, 1.27P  
CASE 483AG



### MARKING DIAGRAM



- |     |                             |
|-----|-----------------------------|
| \$Y | = Logo                      |
| &Z  | = Assembly Location         |
| &3  | = Date Code (Year and Week) |
| &K  | = Specific Device Code      |

### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

**MOSFET MAXIMUM RATINGS**  $T_A = 25^\circ\text{C}$  unless otherwise noted

| Symbol         | Parameter                                             | Rating          | Unit             |
|----------------|-------------------------------------------------------|-----------------|------------------|
| $V_{DS}$       | Drain to Source Voltage                               | 150             | V                |
| $V_{GS}$       | Gate to Source Voltage                                | $\pm 20$        | V                |
| $I_D$          | Drain Current Continuous, $T_C = 25^\circ\text{C}$    | 62              | A                |
|                | Continuous, $T_A = 25^\circ\text{C}$ (Note 1a)        | 10              |                  |
|                | Pulsed (Note 4)                                       | 271             |                  |
| $E_{AS}$       | Single Pulse Avalanche Energy (Note 3)                | 541             | mJ               |
| $P_D$          | Power Dissipation, $T_C = 25^\circ\text{C}$           | 113             | W                |
|                | Power Dissipation, $T_A = 25^\circ\text{C}$ (Note 1a) | 2.7             |                  |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range      | $-55$ to $+150$ | $^\circ\text{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

**THERMAL CHARACTERISTICS**

| Symbol          | Parameter                                         | Rating | Unit                      |
|-----------------|---------------------------------------------------|--------|---------------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case              | 1.1    | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1a) | 45     |                           |

**ELECTRICAL CHARACTERISTICS**  $T_A = 25^\circ\text{C}$  unless otherwise noted

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------|-----------|-----------------|------|------|------|------|
|--------|-----------|-----------------|------|------|------|------|

**OFF CHARACTERISTICS**

|                              |                                           |                                                             |     |     |           |                            |
|------------------------------|-------------------------------------------|-------------------------------------------------------------|-----|-----|-----------|----------------------------|
| $BV_{DSS}$                   | Drain to Source Breakdown Voltage         | $I_D = 250\ \mu\text{A}, V_{GS} = 0\ \text{V}$              | 150 | –   | –         | V                          |
| $\Delta BV_{DSS}/\Delta T_J$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\ \mu\text{A}$ , referenced to $25^\circ\text{C}$ | –   | 109 | –         | $\text{mV}/^\circ\text{C}$ |
| $I_{DSS}$                    | Zero Gate Voltage Drain Current           | $V_{DS} = 120\ \text{V}, V_{GS} = 0\ \text{V}$              | –   | –   | 1         | $\mu\text{A}$              |
| $I_{GSS}$                    | Gate to Source Leakage Current            | $V_{GS} = \pm 20\ \text{V}, V_{DS} = 0\ \text{V}$           | –   | –   | $\pm 100$ | nA                         |

**ON CHARACTERISTICS**

|                                |                                                          |                                                                      |     |      |      |                            |
|--------------------------------|----------------------------------------------------------|----------------------------------------------------------------------|-----|------|------|----------------------------|
| $V_{GS(th)}$                   | Gate to Source Threshold Voltage                         | $V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$                            | 2.0 | 3.0  | 4.0  | V                          |
| $\Delta V_{GS(th)}/\Delta T_J$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D = 250\ \mu\text{A}$ , referenced to $25^\circ\text{C}$          | –   | –11  | –    | $\text{mV}/^\circ\text{C}$ |
| $R_{DS(on)}$                   | Static Drain to Source On Resistance                     | $V_{GS} = 10\ \text{V}, I_D = 10\ \text{A}$                          | –   | 9.5  | 12.4 | m $\Omega$                 |
|                                |                                                          | $V_{GS} = 6\ \text{V}, I_D = 8\ \text{A}$                            | –   | 11.5 | 15.5 |                            |
|                                |                                                          | $V_{GS} = 10\ \text{V}, I_D = 10\ \text{A}, T_J = 125^\circ\text{C}$ | –   | 19   | 25   |                            |
| $g_{FS}$                       | Forward Transconductance                                 | $V_{DS} = 5\ \text{V}, I_D = 10\ \text{A}$                           | –   | 35   | –    | S                          |

**DYNAMIC CHARACTERISTICS**

|           |                              |                                                                       |     |      |      |          |
|-----------|------------------------------|-----------------------------------------------------------------------|-----|------|------|----------|
| $C_{ISS}$ | Input Capacitance            | $V_{DS} = 75\ \text{V}, V_{GS} = 0\ \text{V},$<br>$f = 1\ \text{MHz}$ | –   | 3200 | 4480 | pF       |
| $C_{OOS}$ | Output Capacitance           |                                                                       | –   | 291  | 410  | pF       |
| $C_{rss}$ | Reverse Transfer Capacitance |                                                                       | –   | 11   | 20   | pF       |
| $R_g$     | Gate Resistance              |                                                                       | 0.1 | 0.7  | 2.1  | $\Omega$ |

**SWITCHING CHARACTERISTICS**

|                     |                     |                                                                                                  |                                                  |   |     |    |    |
|---------------------|---------------------|--------------------------------------------------------------------------------------------------|--------------------------------------------------|---|-----|----|----|
| t <sub>d(on)</sub>  | Turn-On Delay Time  | V <sub>DD</sub> = 75 V, I <sub>D</sub> = 10 A,<br>V <sub>GS</sub> = 10 V, R <sub>GEN</sub> = 6 Ω |                                                  | – | 21  | 34 | ns |
| t <sub>r</sub>      | Rise Time           |                                                                                                  |                                                  | – | 4.5 | 10 | ns |
| t <sub>d(off)</sub> | Turn-Off Delay Time |                                                                                                  |                                                  | – | 28  | 45 | ns |
| t <sub>f</sub>      | Fall Time           |                                                                                                  |                                                  | – | 6.2 | 12 | ns |
| Q <sub>g</sub>      | Total Gate Charge   | V <sub>GS</sub> = 0 V to 10 V                                                                    | V <sub>DD</sub> = 75 V,<br>I <sub>D</sub> = 10 A | – | 45  | 63 | nC |
| Q <sub>g</sub>      | Total Gate Charge   | V <sub>GS</sub> = 0 V to 6 V                                                                     |                                                  | – | 29  | 41 | nC |

**ELECTRICAL CHARACTERISTICS** (continued)  $T_A = 25^\circ\text{C}$  unless otherwise noted

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------|-----------|-----------------|------|------|------|------|
|--------|-----------|-----------------|------|------|------|------|

**SWITCHING CHARACTERISTICS**

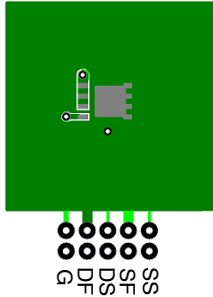
|                 |                               |  |   |     |   |    |
|-----------------|-------------------------------|--|---|-----|---|----|
| Q <sub>gs</sub> | Gate to Source Charge         |  | – | 14  | – | nC |
| Q <sub>gd</sub> | Gate to Drain “Miller” Charge |  | – | 8.8 | – | nC |

**DRAIN-SOURCE DIODE CHARACTERISTICS**

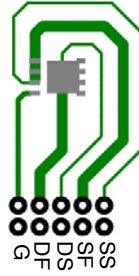
|                 |                                       |                                                        |   |     |     |    |
|-----------------|---------------------------------------|--------------------------------------------------------|---|-----|-----|----|
| V <sub>SD</sub> | Source to Drain Diode Forward Voltage | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 1.9 A (Note 2) | – | 0.7 | 1.2 | V  |
|                 |                                       | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 10 A (Note 2)  | – | 0.8 | 1.3 |    |
| t <sub>rr</sub> | Reverse Recovery Time                 | I <sub>F</sub> = 10 A, di/dt = 100 A/μs                | – | 87  | 139 | ns |
| Q <sub>rr</sub> | Reverse Recovery Charge               |                                                        | – | 165 | 264 | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. R<sub>θJA</sub> is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad with a 1.5 x 1.5 in. board of FR-4 material. R<sub>θJC</sub> is guaranteed by design while R<sub>θCA</sub> is determined by the user's board design.



a. 45°C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.



b. 115°C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. E<sub>AS</sub> of 541 mJ is based on starting T<sub>J</sub> = 25 °C, L = 3 mH, I<sub>AS</sub> = 19 A, V<sub>DD</sub> = 150 V, V<sub>GS</sub> = 10 V. 100% tested at L = 0.1 mH, I<sub>AS</sub> = 60 A.
4. Pulse Id refers to Figure.11 Forward Bias Safe Operation Area.

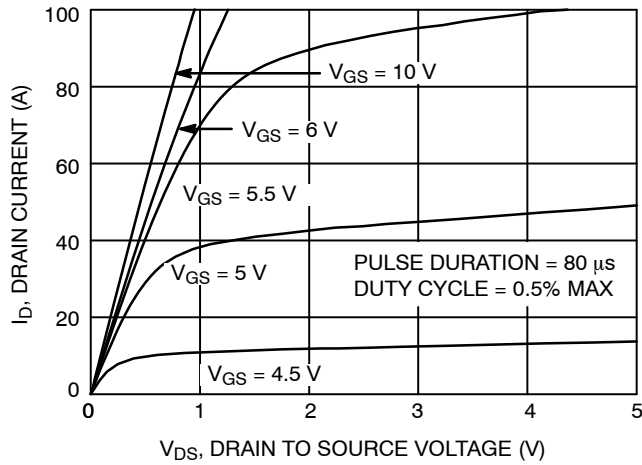
TYPICAL CHARACTERISTICS  $T_J = 25^\circ\text{C}$  unless otherwise noted

Figure 1. On-Region Characteristics

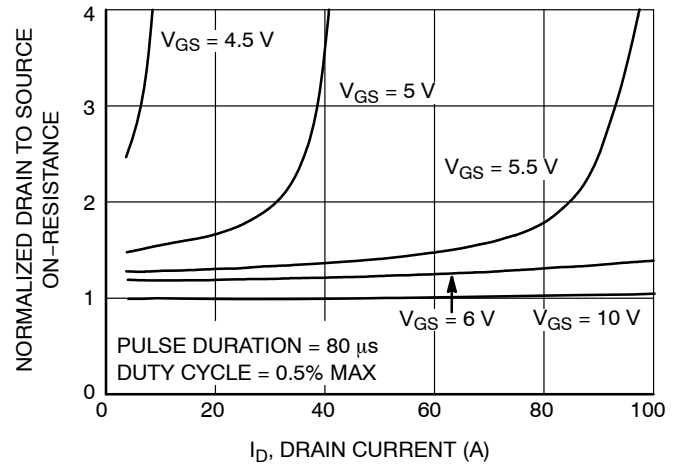


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

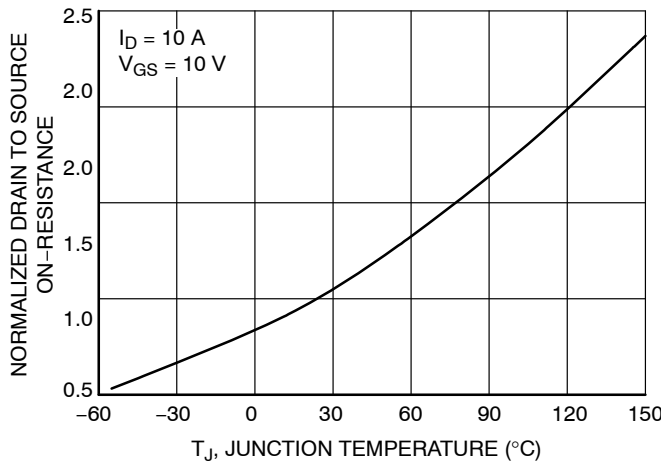


Figure 3. Normalized On-Resistance vs. Junction Temperature

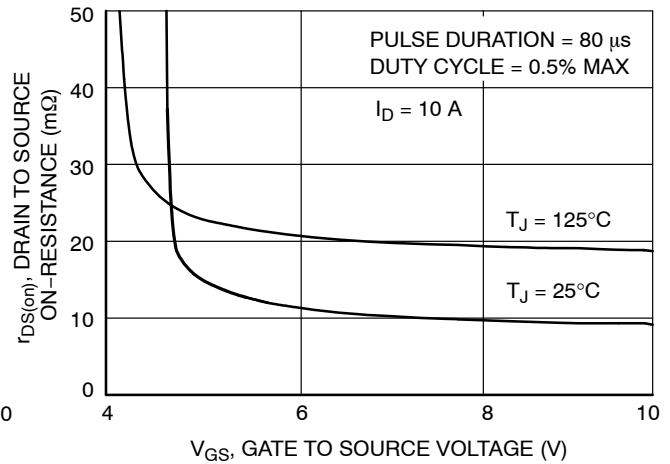


Figure 4. On-Resistance vs. Gate to Source Voltage

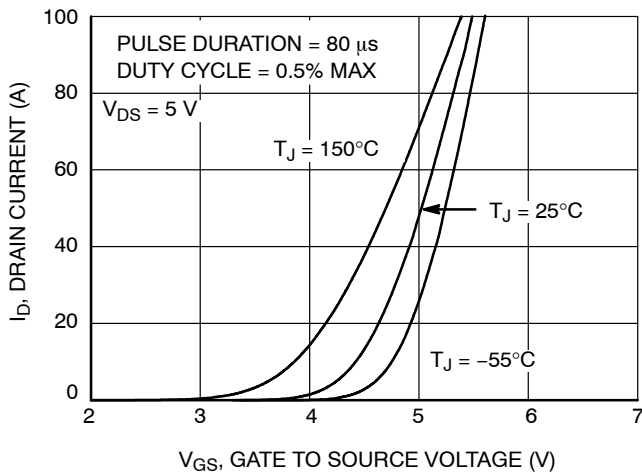


Figure 5. Transfer Characteristics

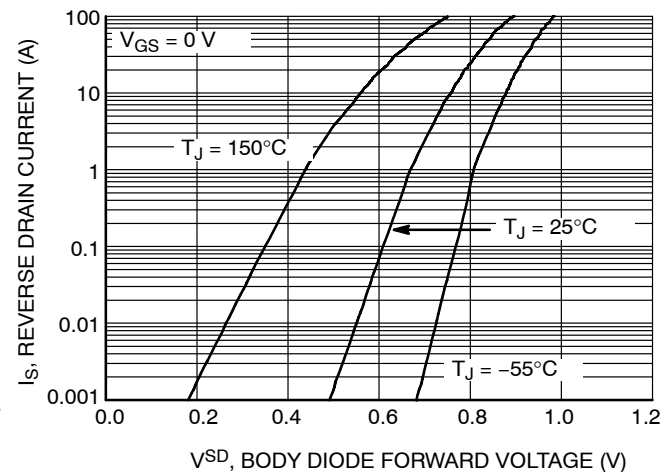


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

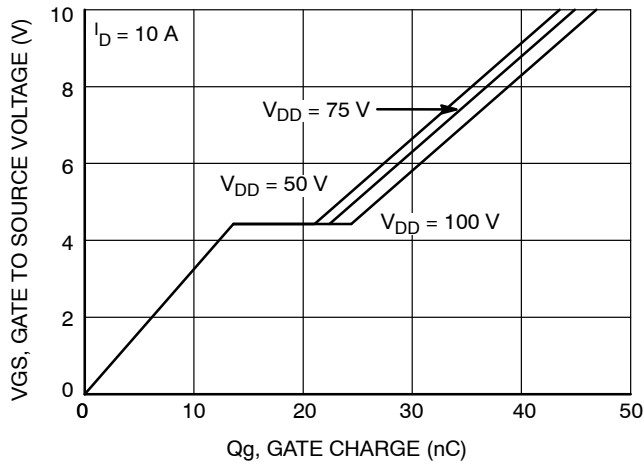
TYPICAL CHARACTERISTICS (continued)  $T_J = 25^\circ\text{C}$  unless otherwise noted

Figure 7. Gate Charge Characteristics

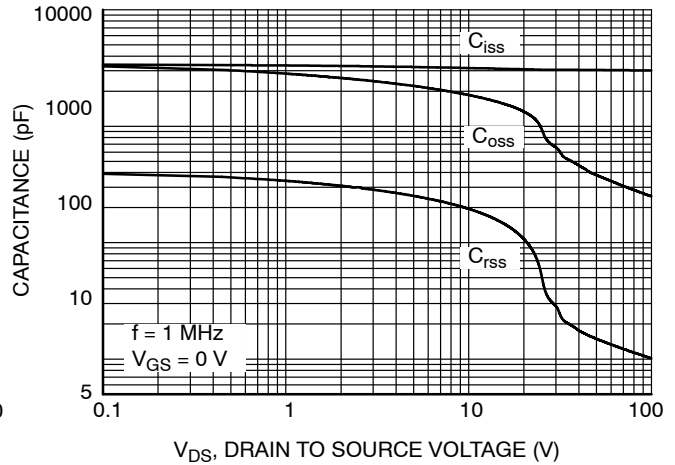


Figure 8. Capacitance vs Drain to Source Voltage

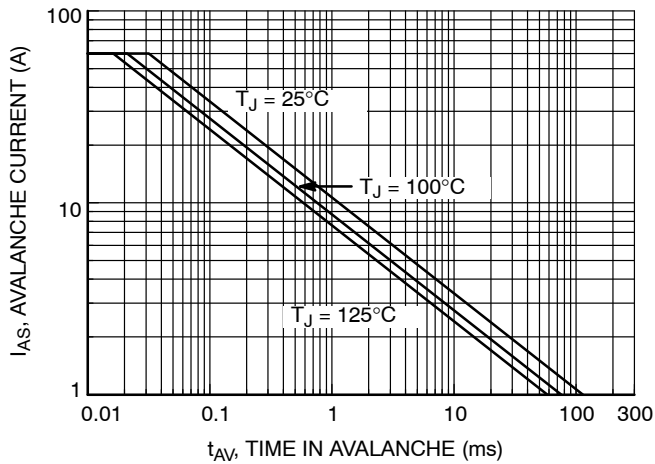


Figure 9. Unclamped Inductive Switching Capability

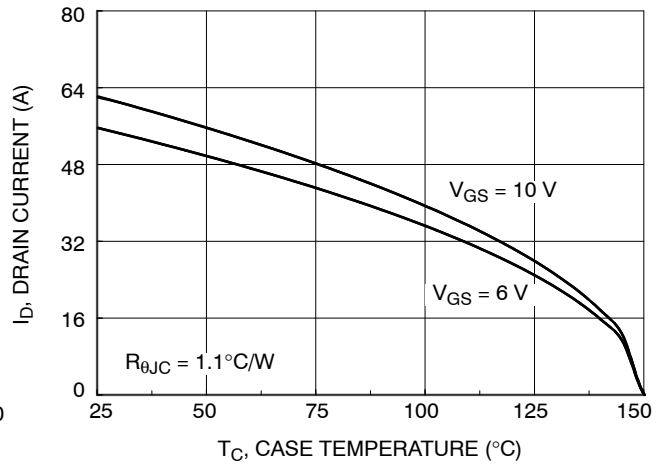


Figure 10. Maximum Continuous Drain Current vs Case Temperature

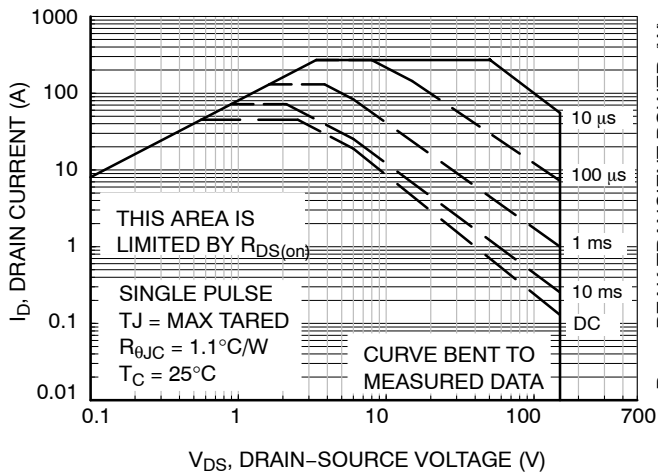


Figure 11. Forward Bias Safe Operating Area

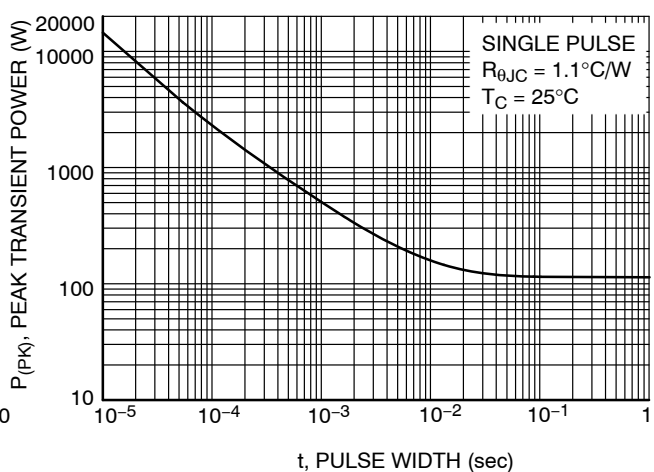
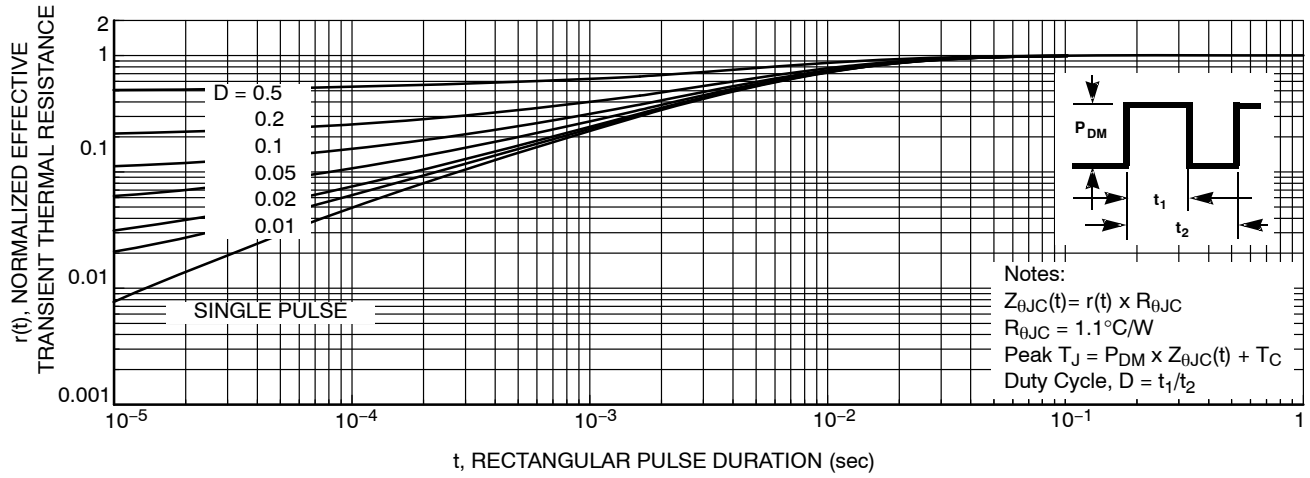


Figure 12. Single Pulse Maximum Power Dissipation

**TYPICAL CHARACTERISTICS** (continued)  $T_J = 25^\circ\text{C}$  unless otherwise noted

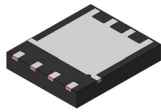


**Figure 13. Transient Thermal Response Curve**

**ORDERING INFORMATION**

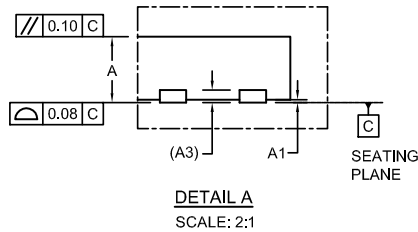
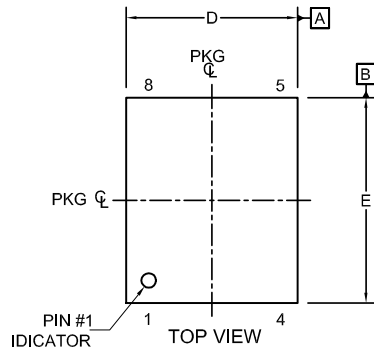
| Device Marking | Device    | Package                 | Reel Size | Tape Width | Shipping <sup>†</sup> |
|----------------|-----------|-------------------------|-----------|------------|-----------------------|
| FDMS86255      | FDMS86255 | PQFN8<br>(Halogen Free) | 13"       | 12 mm      | 3000 / Tape and Reel  |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.



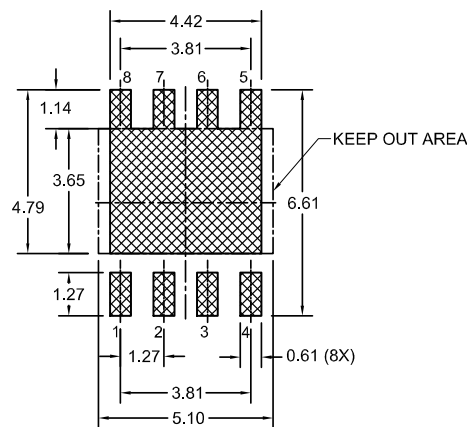
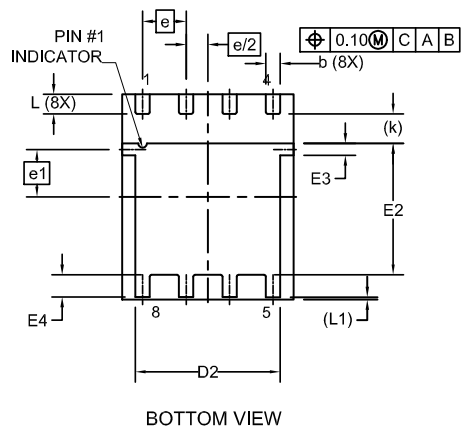
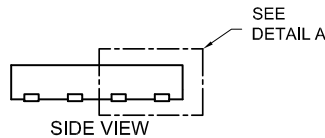
**PQFN8 5X6, 1.27P**  
**CASE 483AG**  
**ISSUE A**

DATE 25 JUN 2021



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
6. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.



\*FOR ADDITIONAL INFORMATION ON OUR  
PB-FREE STRATEGY AND SOLDERING  
DETAILS, PLEASE DOWNLOAD THE ON  
SEMICONDUCTOR SOLDERING AND  
MOUNTING TECHNIQUES REFERENCE  
MANUAL, SOLDERM/D.

| DIM | MILLIMETERS |      |      |
|-----|-------------|------|------|
|     | MIN.        | NOM. | MAX. |
| A   | 0.90        | 1.00 | 1.10 |
| A1  | 0.00        | -    | 0.05 |
| A3  | 0.20 REF    |      |      |
| b   | 0.37        | 0.42 | 0.47 |
| D   | 4.90        | 5.00 | 5.10 |
| D2  | 4.13        | 4.23 | 4.33 |
| E   | 5.90        | 6.00 | 6.10 |
| E2  | 3.74        | 3.84 | 3.94 |
| E3  | 0.25        | 0.35 | 0.45 |
| E4  | 0.60        | 0.70 | 0.80 |
| e   | 1.27 BSC    |      |      |
| e/2 | 0.635 BSC   |      |      |
| e1  | 1.31 BSC    |      |      |
| k   | 0.86 REF    |      |      |
| L   | 0.47        | 0.57 | 0.67 |
| L1  | 0.08REF     |      |      |

**DOCUMENT NUMBER:** 98AON13657G

Electronic versions are uncontrolled except when accessed directly from the Document Repository.  
Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.

**DESCRIPTION:** PQFN8 5X6, 1.27P

**PAGE 1 OF 1**

onsemi and Onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## ADDITIONAL INFORMATION

### TECHNICAL PUBLICATIONS:

Technical Library: [www.onsemi.com/design/resources/technical-documentation](http://www.onsemi.com/design/resources/technical-documentation)  
onsemi Website: [www.onsemi.com](http://www.onsemi.com)

### ONLINE SUPPORT: [www.onsemi.com/support](http://www.onsemi.com/support)

For additional information, please contact your local Sales Representative at  
[www.onsemi.com/support/sales](http://www.onsemi.com/support/sales)